

Transport and magnetic properties of delafossite $\text{CuAl}_{1-x}\text{Mn}_x\text{O}_2$ ceramics

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Wide band gap semiconductors have attracted much attention as a promising class of materials for room temperature ferromagnetism. Recently, both theoretical and experimental works suggest that carrier-mediated ferromagnetism is more favourable with p-type conduction. The delafossite oxide CuAlO_2 is a p-type wide-gap materials with a band gap of ~ 3.5 eV and hole concentration of the order of 10^{17} cm^{-3} . Here we report on the transport and magnetic properties of Mn-doped CuAlO_2 ceramics, synthesized by a standard solid state reaction method in an air atmosphere at a sintering temperature of 1150°C . X-ray diffraction analysis revealed that the equilibrium solubility of Mn ions in CuAlO_2 is as low as about 3 mol%. Nondoped samples were semiconducting with hole concentration of $\sim 5.8 \times 10^{16} \text{ cm}^{-3}$ and the doping of Mn rapidly increased the resistivity. As a result, $\text{CuAl}_{1-x}\text{Mn}_x\text{O}_2$ was strongly insulating for $x = 0.02$ and 0.03 . This suggest that, contrary to common expectations, Mn^{2+} substitution for Al^{3+} in the CuAlO_2 lattice results in oxygen vacancies to maintain charge neutrality, leading to the compensation of existing acceptors. The temperature dependence of the magnetization for $x = 0.02$ showed an almost paramagnetic behavior with a negative Curie-Weiss temperature of about -11 K, indicating an intrinsic antiferromagnetic coupling between Mn ions in CuAlO_2 . The field dependence of the magnetization at 5 K also exhibited no hysteresis shape.

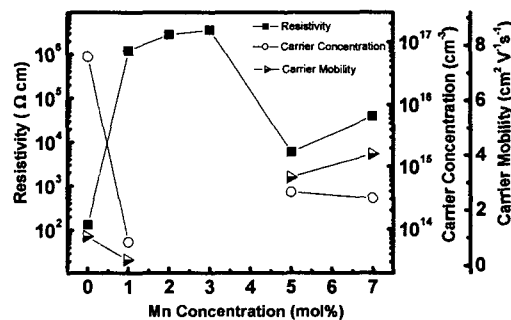


Fig 1. Electrical resistivity, carrier concentration and mobility at room temperature with varying Mn concentration in $\text{CuAl}_{1-x}\text{Mn}_x\text{O}_2$ ceramics ($0 \leq x \leq 0.07$).